

We claim:

1. An electrostatic discharge (ESD) protection device, applied to a mixed voltage circuit assembly, said device comprising:

5 a RC controlled circuit subassembly, coupled with said mixed voltage circuit assembly, utilizing for substantially controlling said ESD protection device to be ON or OFF; and

10 a first transistor, coupled between a first power supply and a second power supply of said mixed voltage circuit assembly, and being coupled to said RC controlled circuit subassembly.

2. The device as recited in claim 1, wherein said RC controlled circuit subassembly comprising:

15 a resistance, one end of said resistance being coupled to the high voltage source of said first power supply; and

a capacitor, coupled to the low voltage source of said second power supply and the other end of said resistance, together with said resistance, utilizing for substantially controlling said first transistor to be ON or OFF.

20 3. The device as recited in claim 2, wherein the RC time constant of said resistance and said capacitor is about 0.1 to 10 μ sec.

4. The device as recited in claim 2, wherein said first transistor is a first PMOS transistor, the gate of said first PMOS transistor being coupled

between said resistance and said capacitor, the source of said first PMOS transistor being coupled to the high voltage source of said first power supply, the drain of said first PMOS transistor being coupled to the high voltage source of said second power supply.

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5. The device as recited in claim 4, wherein said first PMOS transistor is further located in a first N-well, said first N-well being coupled to the high voltage source of said first power supply.

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6. The device as recited in claim 5, further comprising a second PMOS transistor located in a second N-well, the gate of said second PMOS transistor being coupled to the low voltage source of said second power supply, the source of said second PMOS transistor and said second N-well being coupled to the drain of said first PMOS transistor, the drain of said second PMOS transistor being coupled to the high voltage source of said second power supply.

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7. The device as recited in claim 1, wherein said RC controlled circuit subassembly comprising:

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a first resistance, one end of said first resistance being coupled to the high voltage source of said first power supply; and

a first capacitor, coupled to the low voltage source of said second power supply and the other end of said first resistance, together with said first resistance, utilizing for substantially controlling said first transistor to be ON

or OFF.

8. The device as recited in claim 7, wherein the RC time constant of said first resistance and said first capacitor is about 0.1 to 10 μ sec.

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9. The device as recited in claim 8, wherein said first transistor is a first NMOS transistor, the gate of said first NMOS transistor being coupled between said first capacitor and said first resistance, the drain of said first NMOS transistor being coupled to the high voltage source of said first power supply, the source of said first NMOS transistor being coupled to the high voltage source of said second power supply.

10 10. The device as recited in claim 9, wherein said first NMOS transistor is further located in a P-well, said P-well, located in a N-well, being coupled to the high voltage source of said second power supply.

11. The device as recited in claim 9, further comprising a second NMOS transistor, coupled between said first power supply and said second power supply of said mixed voltage circuit assembly, wherein said second NMOS transistor is coupled to said RC controlled circuit subassembly, said first NMOS transistor being conducting and said second NMOS transistor being off as an ESD current entering into said first power supply, said first NMOS transistor being off and said second NMOS transistor being conducting as an ESD current entering into said second power supply.

12. The device as recited in claim 11, wherein said RC controlled circuit subassembly further comprising:

a second capacitor, one end of said second capacitor being coupled to

5 the high voltage source of said second power supply; and

a second resistance, coupled to the low voltage source of said first power supply and the other end of said second capacitor, together with said second capacitor, utilizing for substantially controlling said second NMOS transistor to be ON or OFF.

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13. The device as recited in claim 12, wherein the RC time constant of said second resistance and said second capacitor is about 0.1 to 10 μ sec.

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14. The device as recited in claim 12, wherein the gate of said second

15 NMOS transistor is coupled between said second capacitor and said second resistance, the drain of said second NMOS transistor being coupled to the high voltage source of said second power supply, the source of said second NMOS transistor being coupled to the high voltage source of said first power supply.

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15. The device as recited in claim 11, wherein said first NMOS transistor is further located in a first P-well.

16. The device as recited in claim 11, wherein said second NMOS transistor is further located in a second P-well.

17. An electrostatic discharge (ESD) protection device, applied to a mixed voltage circuit assembly, said device comprising:

a RC controlled circuit subassembly, coupled with said mixed voltage

5 circuit assembly, comprising a resistance and a capacitor, the RC time constant of said resistance and said capacitor is between a rise time of an electrostatic discharge and a rise time of said mixed voltage circuit assembly on a normal power-on condition, utilizing for substantially controlling said ESD protection device to be ON or OFF; and

10 a first PMOS transistor, coupled between a first power supply and a second power supply of said mixed voltage circuit assembly, wherein the gate of said first PMOS transistor is coupled between said resistance and said capacitor, and the source of said first PMOS transistor is coupled to the high voltage source of said first power supply, and the drain of said first PMOS 15 transistor is coupled to the high voltage source of said second power supply.

18. The device as recited in claim 17, wherein one end of said resistance is coupled to the high voltage source of said first power supply, and said capacitor is coupled to the low voltage source of said second power 20 supply and the other end of said resistance, and the RC time constant of said resistance and said capacitor is about 0.1 to 10 μ sec, utilizing for substantially controlling said first PMOS transistor to be ON or OFF.

19. The device as recited in claim 17, wherein said first PMOS

transistor is further located in a first N-well, said first N-well being coupled to the high voltage source of said first power supply.

20. The device as recited in claim 19, further comprising a second
5 PMOS transistor located in a second N-well, the gate of said second PMOS transistor being coupled to the low voltage source of said second power supply, the source of said second PMOS transistor and said second N-well being coupled to the drain of said first PMOS transistor, the drain of said second PMOS transistor being coupled to the high voltage source of said
10 second power supply.

21. An electrostatic discharge (ESD) protection device, applied to a mixed voltage circuit assembly, said device comprising:

a RC controlled circuit subassembly, coupled with said mixed voltage circuit assembly, comprising a first resistance and a first capacitor, the RC time constant of said first resistance and said first capacitor is between a rise time of an electrostatic discharge and a rise time of said mixed voltage circuit assembly on a normal power-on condition, utilizing for substantially controlling said ESD protection device to be ON or OFF; and
20 a first NMOS transistor, coupled between a first power supply and a second power supply of said mixed voltage circuit assembly, wherein the gate of said first NMOS transistor is coupled between said resistance and said capacitor, and the drain of said first NMOS transistor is coupled to the high voltage source of said first power supply, and the source of said first NMOS

transistor is coupled to the high voltage source of said second power supply.

22. The device as recited in claim 21, wherein one end of said first capacitor is coupled to the high voltage source of said first power supply, and
5 said first resistance is coupled to the low voltage source of said second power supply and the other end of said capacitor, and the RC time constant of said first resistance and said first capacitor is about 0.1 to 10 μ sec, utilizing for substantially controlling said first NMOS transistor to be ON or OFF.

10 23. The device as recited in claim 21, wherein said first NMOS transistor is further located in a P-well, said P-well, located in a N-well, being coupled to the high voltage source of said second power supply.

24. The device as recited in claim 22, further comprising:
15 a second capacitor, one end of said second capacitor being coupled to the high voltage source of said second power supply;
a second resistance, being coupled to the low voltage source of said first power supply and the other end of said second capacitor; and
a second NMOS transistor, coupled between said first power supply
20 and said second power supply of said mixed voltage circuit assembly, wherein said second NMOS transistor is coupled between said second capacitor and said second resistance, said first NMOS transistor being conducting and said second NMOS transistor being off as an ESD current entering into said first power supply, said first NMOS transistor being off and said second NMOS

transistor being conducting as an ESD current entering into said second power supply.

25. The device as recited in claim 24, wherein the RC time constant of
5 said second resistance and said second capacitor is about 0.1 to 10 μ sec.

26. The device as recited in claim 24, wherein the gate of said second
NMOS transistor is coupled between said second capacitor and said second
resistance, the drain of said second NMOS transistor being coupled to the high
10 voltage source of said second power supply, the source of said second NMOS
transistor being coupled to the high voltage source of said first power supply.

27. The device as recited in claim 24, wherein said first NMOS
transistor is further located in a first P-well.

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28. The device as recited in claim 24, wherein said second NMOS
transistor is further located in a second P-well.